

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Zhang et al. GROUP: Unknown
SERIAL NO: Unknown EXAMINER: Unknown
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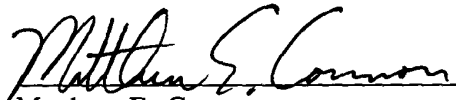
Sir:

INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

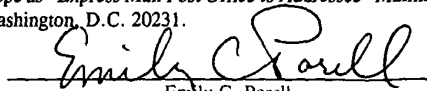
The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that is required.

Respectfully submitted,


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CERTIFICATE OF EXPRESS MAIL UNDER 37 C.F.R. §1.10

I hereby certify that this New Application Transmittal and the documents referred to as enclosed therein are being deposited with the United States Postal Service on July 16, 2003 in an envelope as "Express Mail Post Office to Addressee" Mailing Label Number EV271853740US addressed to the: Assistant Commissioner of Patents, Washington, D.C. 20231.


Emily C. Porell

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
 (Rev. 5/92) 225 Franklin Street, Boston, MA 02110
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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**

7042
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Zhang et al.
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AG	WO 01/67602	09/13/2001	PCT			YES
	AH						
	AI						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AJ	"High-Performance GaAs Switch IC's Fabricated Using MESFET's with Two Kinds of Pinch-Off Voltages and a Symmetrical Pattern Configuration," Uda et al. <i>IEEE Journal of Solid-State Circuits</i> . October 1994. Vol.29, No. 10.
	AK	"A Low-Voltage, High-Power T/R-Switch MMIC Using LC Resonators," Tokumitsu et al. <i>IEEE Transactions on Microwave Theory and Techniques</i> . May 1995. Vol. 43, No. 5.
	AL	"A GaAs High-Power RF Single-Pole Double-Throw Switch IC for Digital Mobile Communication System," Miyatsuji et al. <i>IEEE International Solid-State Circuit Conference</i> . 1994.
	AM	"Novel High Performance SPDT Power Switches Using Multi-Gate FET's," McGrath et al. <i>IEEE MTT-S Digest</i> . 1991.
	AN	"A 3V MMIC hip Set for 1.9GHz Mobile Communication Systems," Tanaka et al. <i>IEEE International Solid-State Circuits Conference</i> . 1995
	AO	"A High Power 2-18 GHz T/R Switch," Schindler et al. <i>IEEE MTT-S Digest</i> . 1990.

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.